

PATENT



FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET 033035 M 0342	SERIAL NO. 10/691,569
	APPLICANTS: Kensaku MOTOKI, et al.	
	FILING DATE October 24, 2003	GROUP ART UNIT 2814

U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
/M.P./	AA	5,828,088	10/27/1998	MAUK			
↓	AB	5,838,029	11/17/1998	SHAKUDA			
↓	AC	5,679,152	10/21/1997	TISCHLER et al.			
↓	AD	5,182,233	01/26/1993	INOUE			
/M.P./	AE	5,770,887	06/23/1998	TADATOMO et al.			
	AF						
	AG						

FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES NO	
	AH							
	AI							
	AJ							
	AK							

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

/M.P./	AL	Office Action for U. S. Patent Application No. 10/691,540 dated April 5, 2005.
/M.P./	AM	IBM, Abstract of "Method of Producing Gallium Nitride Boules for Processing into Substrates," IBM Technical Disclosure Bulletin May 1997, Vol 40, Issue 5, May 1, 1997.
/M.P./	AN	Zheleva et al. "Dislocation density reduction via lateral epitaxy in selectively grown GaN structures," Appl. Phys. Lett. 71 (17) 27 October 1997, pp 2472-2474.
/M.P./	AO	Nam et al. "Lateral epitaxy of low defect density GaN layers via organometallic vapor phase epitaxy," Appl. Phys. Lett. 71 (18), 3 November 1997, pp. 2638-2640.
	AP	
	AQ	

EXAMINER: /Marcos Pizarro Crespo/	DATE CONSIDERED: 08/04/2007
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	